

SEMICONDUCTOR DEVICE ON SILICON-ON-INSULATOR SUBSTRATE

Abstract of Disclosure

A semiconductor device includes a substrate having an active area, a first gate line extending along a first direction on the active area, a first gate line extension adjacent to the first gate line and outside the active area, a second gate line extending along the first direction on the active area and adjacent to the first gate line, and a second gate line extension adjacent to the second gate line and outside the active area. Preferably, the active area includes a first indentation and a second indentation, in which the first gate line extension overlaps the first indentation and the second gate line extension overlaps the first indentation.

Figure 7